1. Scope :

This specification applies to silicon non-zerocrossing phototriac chips,
Device No. ST-1127S

2. Structure :

2-1. Planar type .
2-2. Electrodes :aluminum alloy

3. Size :

3-1. Chip size : 40 mils × 40 mils (1.016 mm ×1.016mm).
3-2. Chip thickness : 12±1.5 mil (0.305± 0.038 mm).
3-3. Pad area : 6 mil dia (0.152 mm dia).
3-4. Pattern drawing : refer to the attached drawing.

4. Electro-optical characteristics (Ta = 25 ℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Peak blocking Current	I_{DRM}	V_{DRM}=800V			500	nA
Peak on-state voltage	V_{TM}	I_{TM}=100mA		1.7	2.2	V
Crittical rate of Rise voltage	dv/dt		1000			V/µS
Holding current	I_H			200		µA